





| Schedule 1:30 – 2:30 III: Partitioning and Floorplanning cont. 2:30 – 3:45 IV: Timing Closure Techniques Integrated timing/synthesis/placement/wiring for ASIC design, placement algorithms, congestion management, use of timing, driven features, timing and routability convergence 3:45 – 4:00 Coffee Break 4:00 – 5:00 V: Analysis and Verification Manufacturability, inductance modeling, IR drop and ground bounce, power analysis and decoupling, signoff timing verification, provided VS/DPC incurse |
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| 5:00 – 5:30 VI: Other Topics Test, formal verification, vendor / tool gossip, your call (based on questionnaire feedback during lunch) |
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| Bus Router | S | |
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And More...

- Other rules
 - Process antenna, phase shift mask, OPC rules

Frameworks

- Channel routing
- Switch box routing
- Maze routing
- Line probe routing
- Shape-based routing
- Fixed die vs. variable die
- Gridded vs. gridless
- This tutorial: Issues, choices (which define methodologies)

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Roadmap Changes Since 2000



| Table 1. 2001 Status of Red Brick Wall | | | | | | | | | |
|---|--|--|--|-------------|--|--|---|--|--|
| Year of production | 2001 | 2003 | 2005 | Sec. | 2007 | 2010 | 2016 | | |
| DRAM half-pitch (nm) | 130 | 100 | 80 | 5 | 65 | 45 | 22 | | |
| Overlay accuracy (nm) | 46 | 35 | 28 | 885 | 23 | 18 | 9 | | |
| MPU gate length (nm) | 90 | 65 | 45 | 88 0 | 35 | 25 | 13 | | |
| CD control (nm) | 8 | 5.5 | 3.9 | | 3.1 | 2.2 | 1.1 | | |
| T _{ex} (equivalent) (nm) | 1.3-1.6 | 1.1-1.6 | 0.8-1.3 | 2017 | 0.6-1.1 | 0.5-0.8 | 0.4-0.5 | | |
| Junction depth (nm) | 48-95 | 33-66 | 24-47 | 264 | 18-37 | 13-26 | 7-13 | | |
| Metal cladding thickness (nm) | 16 | 12 | 9 | | 7 | 5 | 2.5 | | |
| | | | | | | | | | |
| Intermetal dielectric constant, k | 3.0-3.6 | 3.0-3.6 | 2.6-3.1 | | 2.3-2.7 | 2.1 | 1.8 | | |
| Intermetal dielectric constant, k Table 2. 19 | 3.0-3.6 99 St | 3.0-3.6 atus | 2.6-3.1 | d Brick | 23-2.7 Wall | 2.1 | 1.8 | | |
| Intermetal dielectric constant, k Table 2. 19 Year of production | 3.0-3.6 35 St 1999 | 3.0-3.6 atus 2002 | 2.6-3.1 | d Brick | 2.3-2.7 Wall 2008 | 2.1 | 2014 | | |
| Intermetal dielectric constant, k Table 2, 19 Year of production DRAM half-pitch (nm) | 3.0-3.6 99 St 1999 180 | 3.0-3.6 atus 2002 130 | 2.6-3.1 of Re 2005 100 | d Brick | 2.3-2.7 VVall 2008 70 | 2.1 2011 50 | 1.8 2014 35 | | |
| Intermetal dielectric constant, k Table 2. 19 Year of production DRAM half-pitch (nm) Overlay accuracy (nm) | 3.0-3.6 99 St 1999 180 65 | 3.0-3.6 atus 2002 130 45 | 2.6-3.1 of Re 2005 100 35 | ed Brick | 2.3-2.7 C Wall 2008 70 25 | 2.1 2011 50 20 | 1.8 2014 35 15 | | |
| Intermetal dielectric constant, k Table 2. 19 Year of production DRAM half-pitch (nm) Overlay accuracy (nm) MPU gate length (nm) | 3.0-3.6 3.9 St 1999 180 65 140 | 3.0-3.6 atus 2002 130 45 85-90 | 2.6-3.1 of Re 2005 100 35 65 | | 23-2.7 VVall 2008 70 25 45 | 2.1 2011 50 20 30-32 | 1.8 2014 35 15 20-22 | | |
| Intermetal dielectric constant, k Table 2. 19 Year of production DRAM half-pitch (nm) Overlay accuracy (nm) MPU gate length (nm) CD control (nm) | 3.0-3.6 99 St 1999 180 65 140 14 | 3.0-3.6 atus 2002 130 45 85-90 9 | 2.6-3.1 of FRe 2005 100 35 65 65 | | 2.3-2.7 VVall 2008 70 25 45 4 | 2.1 2011 50 20 30-32 3 | 1.8 2014 35 15 20-22 2 | | |
| Intermetal dielectric constant, k Table 2. 199 Year of production DRAM half-pitch (nm) Overlay accuracy (nm) MPU gate length (nm) CD control (nm) T _{ex} (equivalent) (nm) | 3.0-3.6 1999 180 65 140 14 1.9-2.5 | 3.0-3.6 atus 2002 130 45 85-90 9 1.5-1.9 | 2.6-3.1 of Re 2005 100 35 65 6 1.0-1.5 | | 2.3-2.7 VVall 2008 70 25 45 4 0.8-1.2 | 2.1 2011 50 20 30-32 3 0.6-0.8 | 1.8 2014 35 15 20-22 2 0.5-0.6 | | |
| Intermetal dielectric constant, k Table 2, 199 Year of production DRAM half-pitch (nm) Overlay accuracy (nm) MPU gate length (nm) CD control (nm) T _{ox} (equivalent) (nm) Junction depth (nm) | 3.0-3.6 1999 180 65 140 14 1.9-2.5 42-70 | 3.0-3.6 atus 2002 130 45 85-90 9 1.5-1.9 25-43 | 2.6-3.1 of Re 2005 100 35 65 6 1.0-1.5 20-33 | | 2.3-2.7 VVall 2008 70 25 45 4 0.8-1.2 16-26 | 2.1 2011 50 20 30-32 3 0.6-0.8 11-19 | 1.8 2014 35 15 20-22 2 0.5-0.6 8-13 | | |
| Intermetal dielectric constant, k Table 2, 199 Year of production DRAM half-pitch (nm) Overlay accuracy (nm) MPU gate length (nm) CD control (nm) T _{ex} (equivalent) (nm) Junction depth (nm) Metal cladding thickness (nm) | 3.0-3.6 99 St 1999 180 65 140 14 1.9-2.5 42-70 17 | 3.0-3.6 atus 2002 130 45 85-90 9 1.5-1.9 25-43 13 | 2.6-3.1 of Re 2005 100 35 65 6 1.0-1.5 20-33 10 | | 2.3-2.7 VVall 2008 70 25 45 4 0.8-1.2 16-26 0 | 2.1 2011 50 20 30-32 3 0.6-0.8 11-19 0 | 1.8 2014 35 15 20-22 2 0.5-0.6 8-13 0 | | |



| HP / LOP / LSTP Device Roadmaps | | | | | | | | | |
|---------------------------------|--------|------|-------|------------|--------------|------------|-------|-------|-------------|
| Parameter | Туре | 99 | 01 | 03 | 05 | 07 | 10 | 13 | 16 |
| Vdd | MPU | 1.5 | 1.2 | 1.0 | 0.9 | 0.7 | 0.6 | 0.5 | 0.4 |
| | LOP | 1.3 | 1.2 | 1.1 | 1.0 | 0.9 | 0.8 | 0.7 | 0.6 |
| | LSTP | 1.3 | 1.2 | 1.2 | 1.2 | 1.1 | 1.0 | 0.9 | 0.9 |
| Vth (V) | MPU | 0.21 | 0.19 | 0.13 | 0.09 | 0.05 | 0.021 | 0.003 | 0.003 |
| | LOP | 0.34 | 0.34 | 0.36 | 0.33 | 0.29 | 0.29 | 0.25 | 0.22 |
| | LSTP | 0.51 | 0.51 | 0.53 | 0.54 | 0.52 | 0.49 | 0.45 | 0.45 |
| lon (uA/um) | MPU | 1041 | 926 | 967 | 924 | 1091 | 1250 | 1492 | 1507 |
| | LOP | 636 | 600 | 600 | 600 | 700 | 700 | 800 | 900 |
| | LSTP | 300 | 300 | 400 | 400 | 500 | 500 | 600 | 800 |
| CV/I (ps) | MPU | 2.00 | 1.63 | 1.16 | 0.86 | 0.66 | 0.39 | 0.23 | 0.16 |
| | LOP | 3.50 | 2.55 | 2.02 | 1.58 | 1.14 | 0.85 | 0.56 | 0.35 |
| | LSTP | 4.21 | 4.61 | 2.96 | 2.51 | 1.81 | 1.43 | 0.91 | 0.57 |
| loff (uA/um) | MPU | 0.00 | 0.01 | 0.07 | 0.30 | 1.00 | 3 | 7 | 10 |
| | LOP | 1e-4 | 1e-4 | 1e-4 | 3e-4 | 7e-4 | 1e-3 | 3e-3 | 1e-2 |
| | LSTP | 1e-6 | 1e-6 | 1e-6 | 1e-6 | 1e-6 | 3e-6 | 7e-6 | 1e-5 |
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System Complexity Challenges

- System Complexity = exponentially increasing transistor counts, with increased diversity (mixed-signal SOC, ...)
- Reuse (hierarchical design support, heterogeneous SOC integration, reuse of verification/test/IP)
- Verification and test (specification capture, design for verifiability, verification reuse, system-level and software verification, AMS self-test, noise-delay fault tests, test reuse)
- Cost-driven design optimization (manufacturing cost modeling and analysis, quality metrics, die-package co-optimization, ...)
- Embedded software design (platform-based system design methodologies, software verification/analysis, codesign w/HW)
- Reliable implementation platforms (predictable chip implementation onto multiple fabrics, higher-level handoff)
- Design process management (team size / geog distribution, data mgmt, collaborative design, process improvement)

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Noise

Analog design concerns are due to physical noise sources

 because of discreteness of electronic charge and stochastic nature of electronic transport processes

- example: thermal noise, flicker noise, shot noise
- Digital circuits due to large, abrupt voltage swings, create deterministic noise which is several orders of magnitude higher than stochastic physical noise
 - still digital circuits are prevalent because they are inherently immune to noise
- Technology scaling and performance demands make noisiness of digital circuits a big problem







Planning Technology Elements

- RTL partitioning
 - understand interaction b/w block definition and placement quality
 - recognize and cure a physically challenged logic hierarchy
- Global interconnect planning and optimization
 - symbolic route representations to support block plan ECOs
- Controllable SP&R back end (including power/clock/scan)
- Incremental / ECO optimizations, and optimizations that are "robust" under partial or imperfect design knowledge
- Better estimators ("initial WLMs")
 - to account for resource, topological heterogeneity
 - to account for optimizations (placement, ripup/reroute, timing)
- → "earliest RTL signoff with detailed P&R knowledge"

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Taxonomy of Traditional Planning / Implementation Methodologies

- Centered on logic design
 - wire-planning methodology with block/cell global placement
 - global routing directives passed forward to chip finishing
 - constant-delay methodology may be used to guide sizing
- Centered on physical design
 - placement-driven or placement-knowledgeable logic synthesis
- Buffer between logic and layout synthesis
 - placement, timing, sizing optimization tools
- Centered on SOC, chip-level planning
 - interface synthesis between blocks
 - communications protocol, protocol implementation decisions guide logic and physical implementation

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Issue: Performance Optimizations Design optimizations global restructuring optimization -- logic optimization on layout using actual RC, noise peak values etc. localized optimization -- with no structural changes and least layout impact repeater/buffer insertion for global wires Physical optimizations high fanout net synthesis (eg. for clock nets); buffer trees to meet delay/skew and fanout requirements automatically determine network topology (# levels, #buffers, and type of buffers) wire sizing, spacing, shielding etc. Fixing timing violations automatically fix setup/hold time violations fix maximum slew and fanout violations ASPDAC03 - Physical Chip Implementation 40 Jan. 2003 Courtesy Hormoz/Muddu, ASIC99







Placement Directions

- Global placement
 - Engines (analytic, top-down partitioning based, (iterative annealing based) remain the same; all support "anytime" convergent solution
 - Several hybrid ideas (multilevel, force-directed, quadratic + partition)
 - Becomes more hierarchical

 block placement, latch placement before "cell placement"
 - Supports placement of partially/probabilistically specified design
- Detailed placement
 - LEQ/EEQ substitution
 - Shifting, spacing and alignment for routability
 - ECOs for timing, signal integrity, reliability
 - Closely tied to performance analysis backplane (STA/PV)
 - Supports incremental "construct by correction" use model



- Router ultimately responsible for meeting specs/assumptions
 - Slew, noise, delay, critical-area, antenna ratio, PSM-amenable ...
- Checks performability throughout top-down physical impl.
 - Actively understands, invokes analysis engines and macromodels
- Many functions
 - Circuit-level IP generation: clock, power, test, package substrate routing
 - Pin assignment and track ordering engines
 - "Monolithic" (entire net at a time) topology optimization engines
 - <u>Owns</u> key DOFs: small re-mapping, incremental placement, devicelevel layout resynthesis
 - Is hierarchical, scalable, incremental, controllable, well-characterized (well-modeled), detunable (e.g., coarse/quick routing), ...

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